

MAGX-000025-150000



GaN on SiC HEMT Power Transistor
150 W, 1-2500 MHz

Rev. V1

Features

- GaN on SiC Transistor Technology
- Broadband Unmatched Transistor
- Common-Source Configuration
- +50 V Typical Operation
- Class AB Operation
- RoHS* Compliant and 260°C Reflow Compatible
- MTTF = 600 years ($T_J < 200\text{ }^{\circ}\text{C}$)

Applications

- General purpose for pulsed or CW applications

Description

The MAGX-000025-150000 is a gold-metalized Gallium Nitride (GaN) on Silicon Carbide (SiC) RF power transistor suitable for a variety of RF power amplifier applications. Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, and ruggedness over a wide bandwidth for today's demanding application needs. High breakdown voltages allow for reliable and stable operation under more extreme mismatch load conditions compared with older semiconductor technologies.

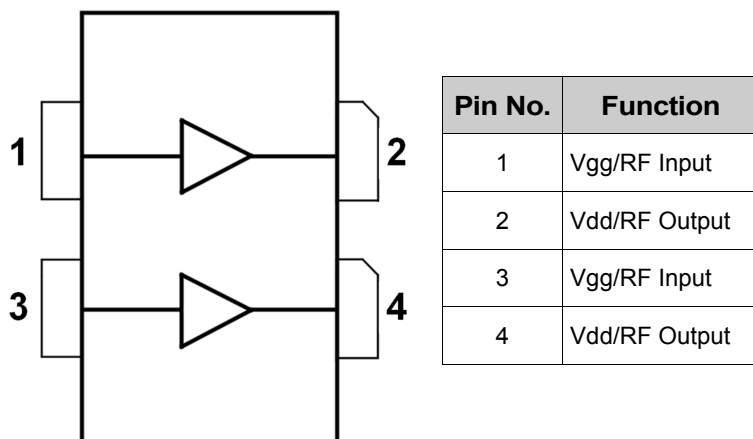
MAGX-000025-150000



Ordering Information

Part Number	Description
MAGX-000025-150000	Flanged
MAGX-000025-SB2PPR	1200-1400 MHz Evaluation Board
MAGX-000025-SB1PPR	2500 MHz Evaluation Board

Functional Schematic



* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

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Electrical Specifications¹: Freq. = 1200-1400 MHz, T_A = 25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
RF Functional Tests: V_{DD} = 50 V, I_{DQ} = 600 mA, 300 μs Pulse, 20% Duty						
Output Power	P _{IN} = 2.5 W	P _{OUT}	150	170	-	W
Power Gain	P _{IN} = 2.5 W	G _P	17.5	18	-	dB
Drain Efficiency	P _{IN} = 2.5 W	η _D	52	58	-	%
Droop	P _{IN} = 2.5 W	Droop	-	0.2	0.3	dB
Load Mismatch Stability	P _{IN} = 2.5 W	VSWR-S	-	5:1	-	-
Load Mismatch Tolerance	P _{IN} = 2.5 W	VSWR-T	-	10:1	-	-

Typical RF Characteristics²: Freq. = 2500 MHz, T_A = 25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
RF Functional Tests: V_{DD} = 50 V, I_{DQ} = 600 mA, 300 μs Pulse, 20% Duty						
Output Power	P _{IN} = 7 W	P _{OUT}	-	125	-	W
Power Gain	P _{IN} = 7 W	G _P	-	12.5	-	dB
Drain Efficiency	P _{IN} = 7 W	η _D	-	48	-	%
Droop	P _{IN} = 7 W	Droop	-	0.1	-	dB
Load Mismatch Stability	P _{IN} = 7 W	VSWR-S	-	5:1	-	-
Load Mismatch Tolerance	P _{IN} = 7 W	VSWR-T	-	10:1	-	-
RF Functional Tests: V_{DD} = 28 V, I_{DQ} = 600 mA, CW						
Input Power	P _{OUT} = 35 W	P _{IN}	-	2	-	W
Power Gain	P _{OUT} = 35 W	G _P	-	12	-	dB
Drain Efficiency	P _{OUT} = 35 W	η _D	-	45	-	%
Load Mismatch Stability	P _{OUT} = 35 W	VSWR-S	-	5:1	-	-
Load Mismatch Tolerance	P _{OUT} = 35 W	VSWR-T	-	10:1	-	-

Electrical Characteristics³: T_A = 25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
DC Characteristics (Per Side):						
Drain-Source Leakage Current	V _{GS} = -8 V, V _{DS} = 175 V	I _{DS}	-	2	5.28	mA
Gate Threshold Voltage	V _{DS} = 5 V, I _D = 75 mA	V _{GS(TH)}	-5	-3.1	-2	V
Forward Transconductance	V _{DS} = 5 V, I _D = 17.5 mA	G _M	2	2.8	-	S
Dynamic Characteristics (Per Side):						
Input Capacitance	V _{DS} = 0 V, V _{GS} = -8 V, F = 1 MHz	C _{ISS}	-	26.4	-	pF
Output Capacitance	V _{DS} = 50 V, V _{GS} = -8 V, F = 1 MHz	C _{OSS}	-	11.2	-	pF
Reverse Transfer Capacitance	V _{DS} = 50 V, V _{GS} = -8 V, F = 1 MHz	C _{RSS}	-	1	-	pF

1. Electrical Specifications measured in MACOM RF evaluation board.

2. Typical RF Characteristics measured in MACOM RF evaluation board.

3. All DC Characteristics are per side.

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Absolute Maximum Ratings^{4,5,6,7,8}

Parameter	Limit
Supply Voltage (V_{DD})	+65 V
Supply Voltage (V_{GS})	-8 to -2 V
Supply Current ($I_{D_{MAX}}$) for CW operation at $V_{DD} = 28$ V	5.5 A
Supply Current ($I_{D_{MAX}}$) for pulsed operation at $V_{DD} = 50$ V	8.3 A
Input Power (P_{IN}) for CW operation at $V_{DD} = 28$ V	P_{IN} (typical) + 1.5 dB
Input Power (P_{IN}) for pulsed operation at $V_{DD} = 50$ V	40 dBm
Absolute Max. Junction/Channel Temperature	200°C
Power Dissipation at 85 °C for CW operation at $V_{DD} = 28$ V	79 W
Power Dissipation at 85 °C for pulsed operation at $V_{DD} = 50$ V	177 W
Thermal Resistance, ($T_J = 200$ °C) $V_{DD} = 28$ V, $I_{DQ} = 600$ mA, $P_{out} = 35$ W, CW	1.45 °C/W
Thermal Resistance, ($T_J = 200$ °C) $V_{DD} = 50$ V, $I_{DQ} = 600$ mA, $P_{in} = 7$ W, pulsed	0.65 °C/W
Operating Temperature	-40 to +95°C
Storage Temperature	-65 to +150°C
Mounting Temperature	See solder reflow profile
ESD Min. - Charged Device Model (CDM)	300 V
ESD Min. - Human Body Model (HBM)	700 V

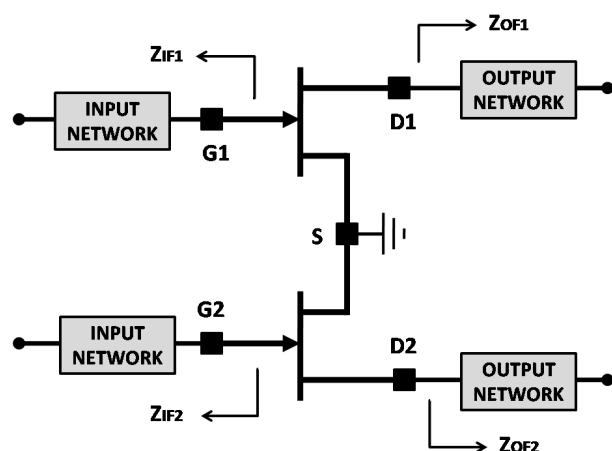
4. Operation of this device above any one of these parameters may cause permanent damage.
5. For CW operation, Input Power limit is +1.5 dB over nominal drive required to achieve $P_{OUT} = 35$ W.
6. Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.
7. For saturated performance it is recommended that the sum of $(3 \cdot V_{DD} + \text{abs}(V_{GG})) < 175$ V.
8. Pulsed operation is specified for a 300 μ s Pulse, 20% Duty.

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Test Fixture Impedances (Per Side)

F (MHz)	$Z_{IF(1,2)} (\Omega)$	$Z_{OF(1,2)} (\Omega)$
1200	$0.8 + j0.5$	$9.4 + j4.1$
1300	$0.9 + j0.2$	$7.2 + j3.0$
1400	$0.5 - j0.2$	$5.4 + j3.4$
2500	$1.2 - j3.4$	$3.1 + j1.4$



Correct Device Sequencing

Turning the device ON

1. Set V_{GS} to the pinch-off (V_P), typically -5 V.
2. Turn on V_{DS} to nominal voltage:
[(300 μ s, 20%) = 50 V; (2.5 GHz, CW) = 28 V].
3. Increase V_{GS} until the I_{DS} current is reached.
4. Apply RF power to desired level.

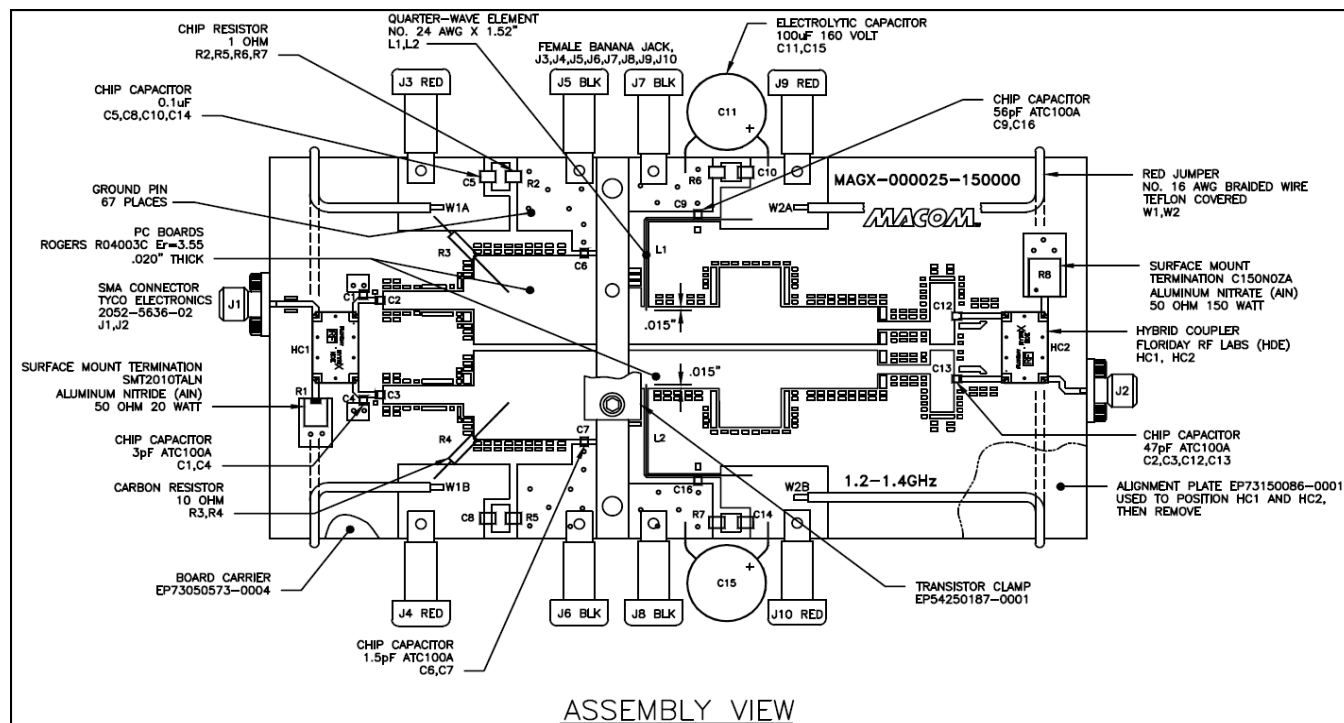
Turning the device OFF

1. Turn the RF power off.
2. Decrease V_{GS} down to V_P .
3. Decrease V_{DS} down to 0 V.
4. Turn off V_{GS} .

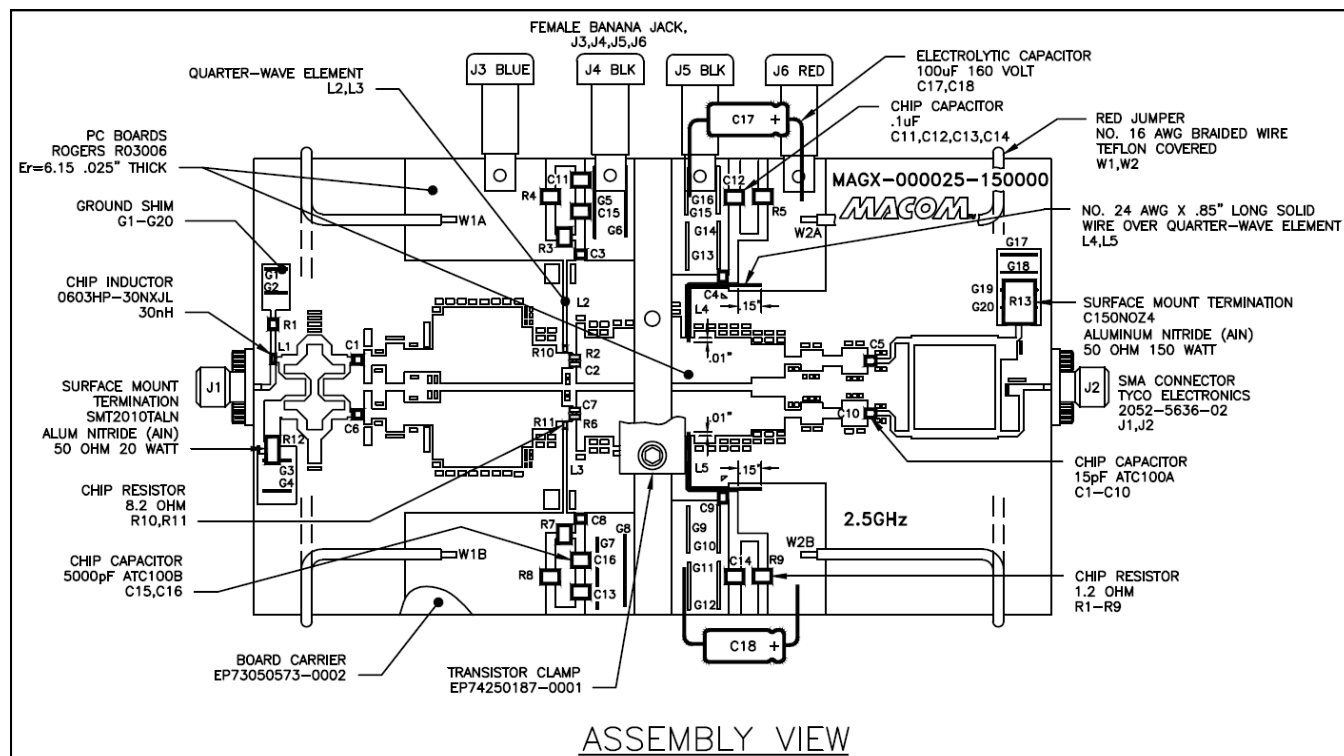
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Test Fixture Assembly (1200-1400 MHz)



Test Fixture Assembly (2500 MHz)

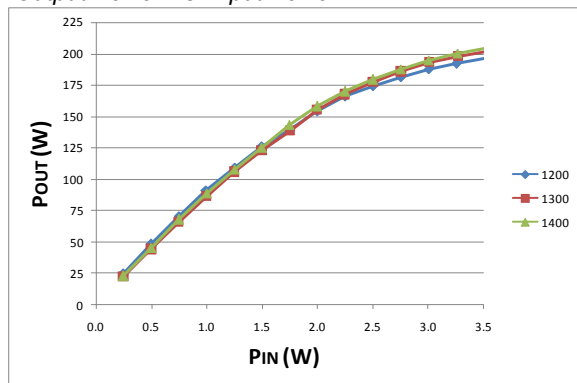


Application Section

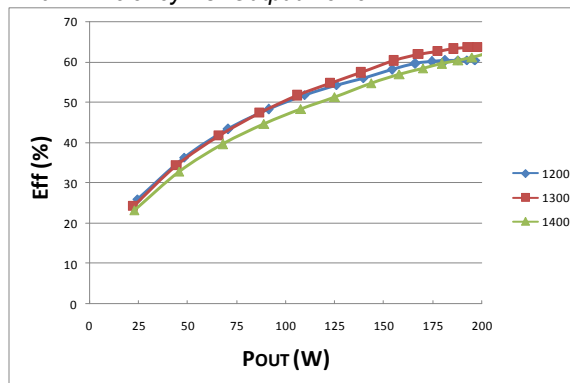
Typical Performance Curves

1200-1400 MHz, 300 μ s Pulse, 20% Duty, $V_{DD} = 50$ V, $I_{dq} = 600$ mA

Output Power Vs. Input Power

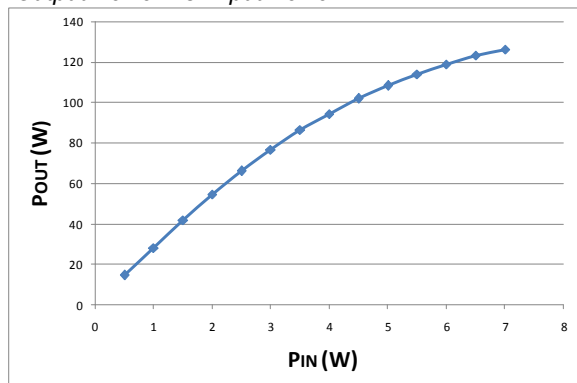


Drain Efficiency Vs. Output Power

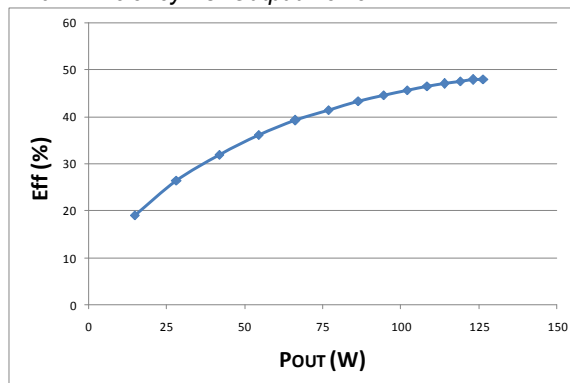


2500 MHz, 300 μ s Pulse, 20% Duty, $V_{DD} = 50$ V, $I_{dq} = 600$ mA

Output Power Vs. Input Power

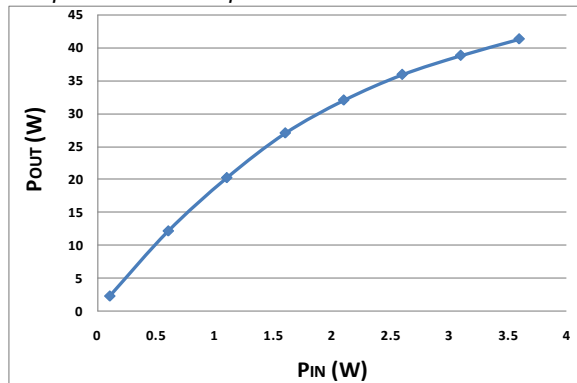


Drain Efficiency Vs. Output Power

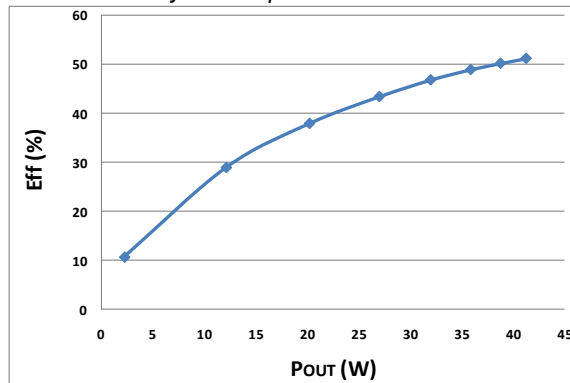


2500 MHz, CW, $V_{DD} = 28$ V, $I_{dq} = 600$ mA

Output Power Vs. Input Power



Drain Efficiency Vs. Output Power



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Technical drawing of a MOSFET package, showing top and side views with dimensions in inches and millimeters.

Top View Dimensions:

- Overall width: 1.140" [28.96]
- Distance between drain pins: .900" [22.86]
- Distance between gate pins: .215" [5.46]
- Distance between source pins: .260" [6.60]
- Pin pitch (GATE): .235" [5.97]
- Pin pitch (DRAIN): .235" [5.97]
- Pin pitch (SOURCE): .230" [5.84]
- Pin diameter: 2X $\phi .130$
- Part number: MACOM GX0025-150
- Lot number: LOT NO. / SER NO.

Side View Dimensions:

- Package height: .188" $\pm .010$ " [4.78 ± 0.25]
- Gate pin height: .082" $\pm .010$ " [2.08 ± 0.25]
- Drain pin height: .650" [16.51]
- Source pin height: .060" [1.52]
- Source pin thickness: 4X .005" $\pm .001$ " [0.13 ± 0.03]

Unless otherwise noted, tolerances are inches $\pm .005$ " [millimeters ± 0.13 mm]